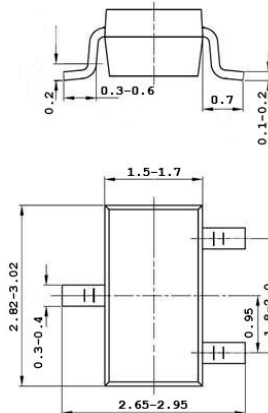
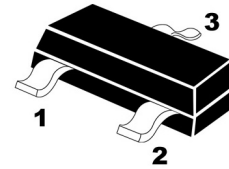


TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

- Excellent h_{FE} linearity:
 $h_{FE(2)} = 25(\text{min})$ at $V_{CE} = -6V$, $I_C = -400\text{mA}$
- High voltage: $V_{CEO} = -50V(\text{min})$
- Complements the 2SC3325

MARKING: ACO, ACY
SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR



Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA
Base Current	I_B	-50	mA
Collector Dissipation	P_C	200	mW
Junction and Storage Temperature	T_J, T_{stg}	-55-150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100\text{mA}$	70		240	
	$h_{FE(2)}$	$V_{CE} = -6V, I_C = -400\text{mA}$	25			
			40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.25	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1V, I_C = -100\text{mA}$			-1	V
Transition Frequency	f_T	$V_{CE} = -6V, I_C = -20\text{mA}$		200		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -6V, I_E = 0, f = 1\text{MHz}$		13		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240

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